

NS2029M3

PNP Silicon General Purpose Amplifier Transistor

This PNP transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE} , 210–460 (Typical)
- Low $V_{CE(sat)}$, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 8000 Unit Tape & Reel with 2 mm Pitch
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

| Rating | Symbol | Value | Unit |
|--------------------------------|---------------|-------|------|
| Collector-Base Voltage | $V_{(BR)CBO}$ | -60 | Vdc |
| Collector-Emitter Voltage | $V_{(BR)CEO}$ | -50 | Vdc |
| Emitter-Base Voltage | $V_{(BR)EBO}$ | -6.0 | Vdc |
| Collector Current - Continuous | I_C | -150 | mAdc |

THERMAL CHARACTERISTICS

| Rating | Symbol | Max | Unit |
|----------------------------|-----------|------------|------------------|
| Power Dissipation (Note 1) | P_D | 265 | mW |
| Junction Temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -55 ~ +150 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

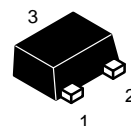
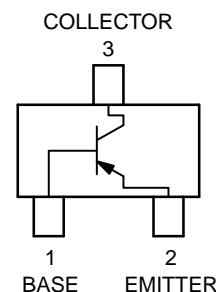
1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



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PNP GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



SOT-723
CASE 631AA

MARKING DIAGRAM



9F = Specific Device Code
M = Date Code*

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|-------------------|------------------|
| NS2029M3T5G | SOT-723 (Pb-Free) | 8000/Tape & Reel |
| NSV2029M3T5G | SOT-723 (Pb-Free) | 8000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NS2029M3

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|---------------|------|-----|------|---------------|
| Collector–Base Breakdown Voltage ($I_C = -50 \mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | -60 | - | - | Vdc |
| Collector–Emitter Breakdown Voltage ($I_C = -1.0 \text{mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | -50 | - | - | Vdc |
| Emitter–Base Breakdown Voltage ($I_E = -50 \mu\text{A}$, $I_C = 0$) | $V_{(BR)EBO}$ | -6.0 | - | - | Vdc |
| Collector–Base Cutoff Current ($V_{CB} = -30 \text{Vdc}$, $I_E = 0$) | I_{CBO} | - | - | -0.5 | nA |
| Emitter–Base Cutoff Current ($V_{EB} = -7.0 \text{Vdc}$, $I_B = 0$) | I_{EBO} | - | - | -0.1 | μA |
| Collector–Emitter Saturation Voltage (Note 2) ($I_C = -50 \text{mA}$, $I_B = -5.0 \text{mA}$) | $V_{CE(sat)}$ | - | - | -0.5 | Vdc |
| DC Current Gain (Note 2) ($V_{CE} = -6.0 \text{Vdc}$, $I_C = -1.0 \text{mA}$) | h_{FE} | 120 | - | 560 | - |
| Transition Frequency ($V_{CE} = -12 \text{Vdc}$, $I_C = -2.0 \text{mA}$, $f = 30 \text{MHz}$) | f_T | - | 140 | - | MHz |
| Output Capacitance ($V_{CB} = -12 \text{Vdc}$, $I_E = 0 \text{A}$, $f = 1.0 \text{MHz}$) | C_{OB} | - | 3.5 | - | pF |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

TYPICAL ELECTRICAL CHARACTERISTICS

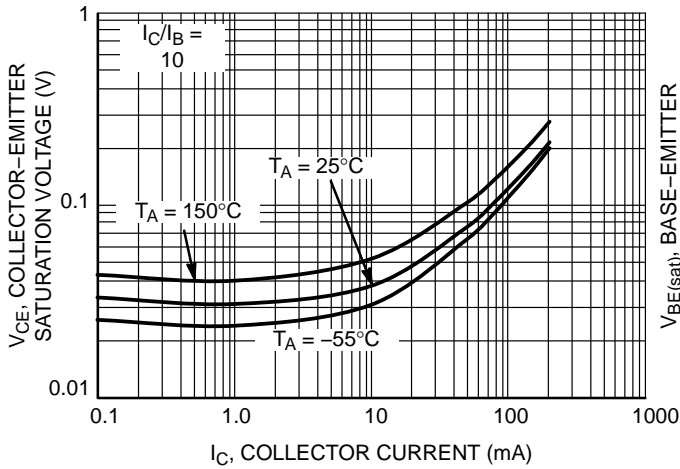


Figure 1. Collector-Emitter Saturation Voltage vs. Collector Current

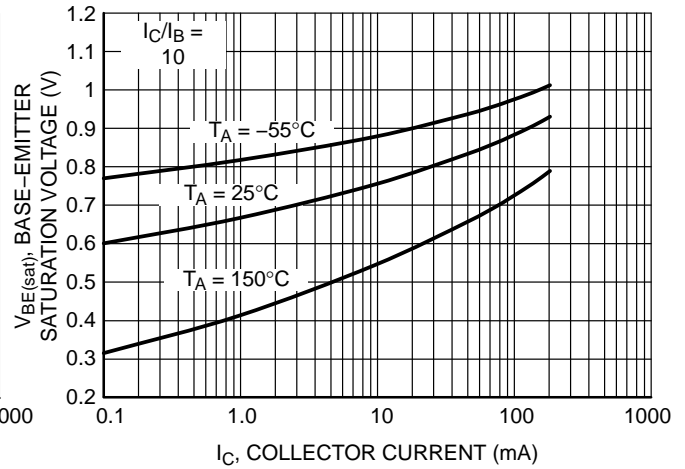


Figure 2. Base-Emitter Saturation Voltage vs. Collector Current

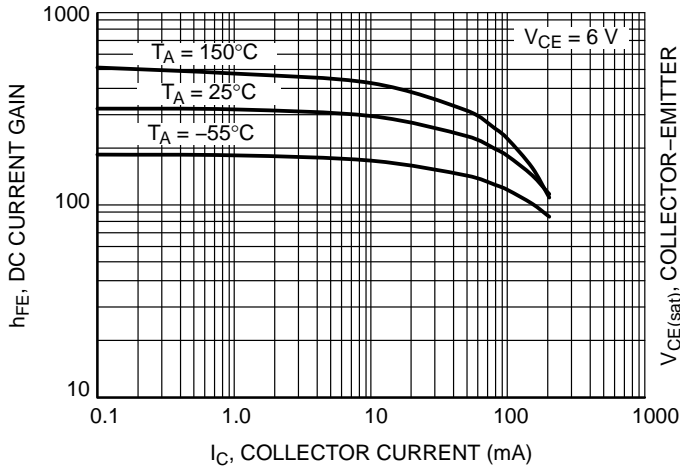


Figure 3. DC Current Gain vs. Collector Current

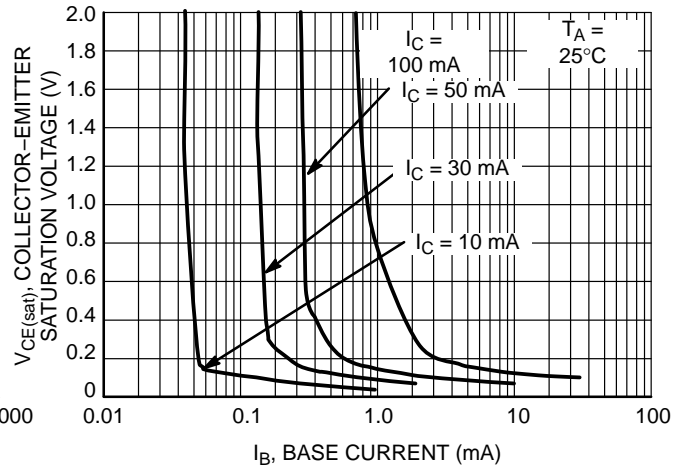


Figure 4. Saturation Region

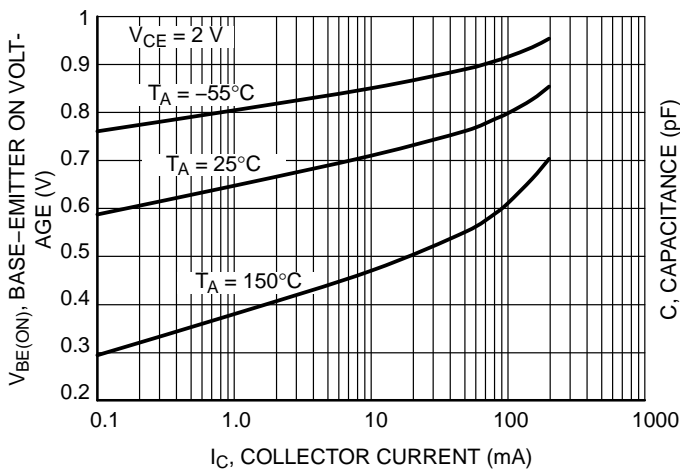


Figure 5. Base-Emitter Turn-ON Voltage vs. Collector Current

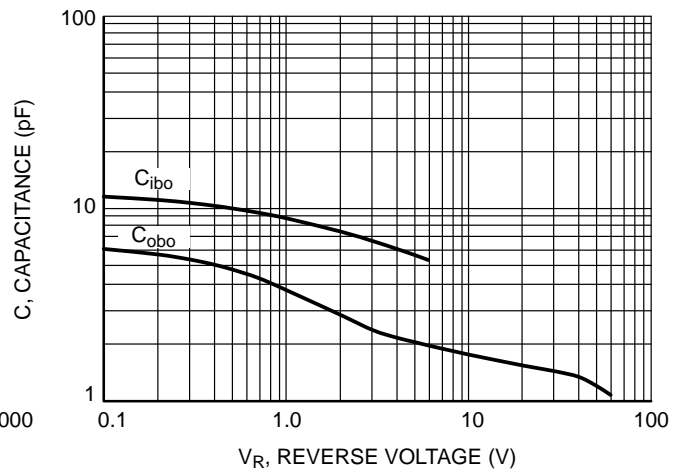


Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

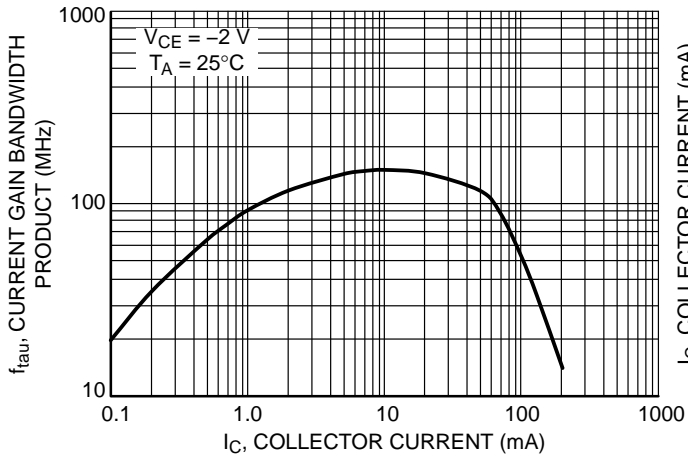


Figure 7. Current Gain Bandwidth Product vs. Collector Current

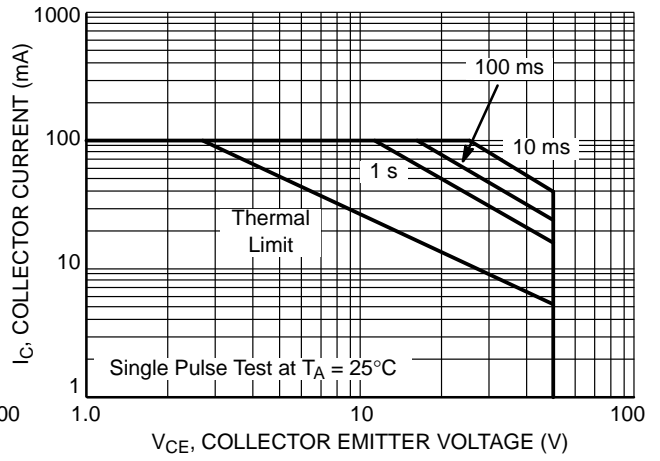
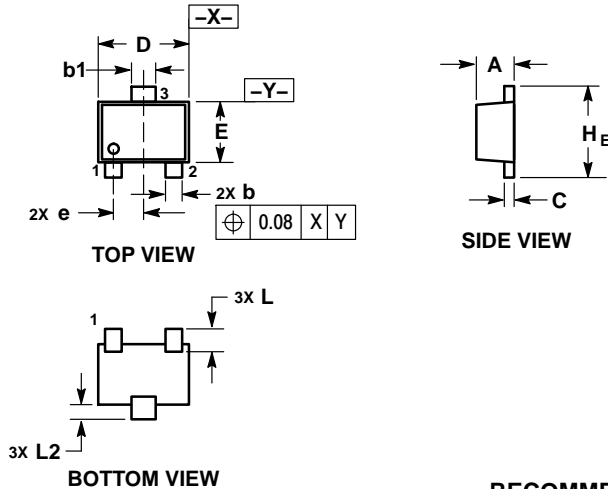


Figure 8. Safe Operating Area

NS2029M3

PACKAGE DIMENSIONS

SOT-723
CASE 631AA
ISSUE D

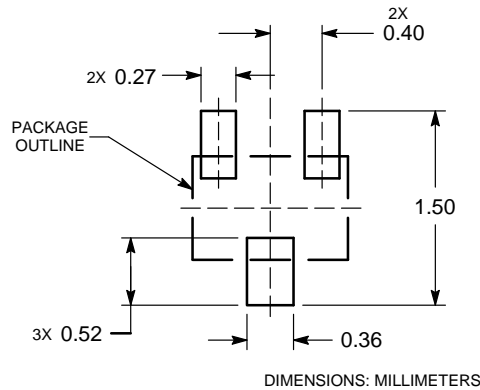


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

| DIM | MILLIMETERS | | |
|----------------|-------------|------|------|
| | MIN | NOM | MAX |
| A | 0.45 | 0.50 | 0.55 |
| b | 0.15 | 0.21 | 0.27 |
| b1 | 0.25 | 0.31 | 0.37 |
| C | 0.07 | 0.12 | 0.17 |
| D | 1.15 | 1.20 | 1.25 |
| E | 0.75 | 0.80 | 0.85 |
| e | 0.40 BSC | | |
| H _E | 1.15 | 1.20 | 1.25 |
| L | 0.29 REF | | |
| L2 | 0.15 | 0.20 | 0.25 |

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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